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Substitute Form PTO-1449 U.S. Department of Commerce (Modified) Patent and Trademark Office	Attorney's Docket No. 10559–586002	Application No.
Information Disclosure Statement by Applicant	Applicant	9
(Use several sheets if necessary) (37 CFR §1.98(b))	Filing Date March 16, 2004	Group Art Unit

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Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate	
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